MITSUBISHI SEMICONDUCTOR <GaAs FET>

MGFC39V6472A

6.4 ~ 7.2GHz BAND 8W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC39V6472A is an internally impedance-matched GaAs power FET especially designed for use in 6.4 ~ 7.2 GHz band amplifiers. The hermetically sealed metalceramic package guarantees high reliability.

FEATURES

Class A operation Internally matched to 50(ohm) system High output power P1dB = 8W (TYP.) @ f=6.4~7.2GHz High power gain GLP = 9 dB (TYP.) @ f=6.4~7.2GHz High power added efficiency P.A.E. = 28 % (TYP.) @ f=6.4~7.2GHz Low distortion [item -51] IM3= -45 dBc(TYP.) @Po=28dBm S.C.L.

APPLICATION

item 01 : 6.4~7.2 GHz band power amplifier item 51 : 6.4~7.2 GHz band digital radio communication

QUALITY GRADE

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RECOMMENDED BIAS CONDITIONS

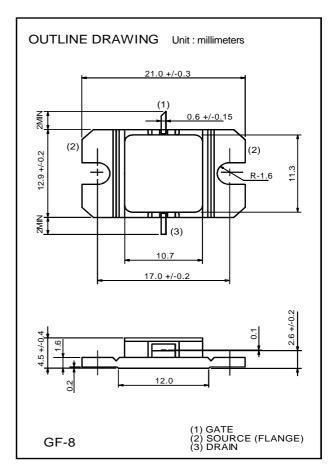
VDS = 10 (V)ID = 2.4 (A)Refer to Bias Procedure" RG= 50 (ohm)

ABSOLUTE MAXIMUM RATINGS (Ta=25 deg.C)

Symbol	Parameter	Ratings	Unit	
VGDO	Gate to drain voltage	-15	V	
VGSO	Gate to source voltage	-15	V	
ID	Drain current	7.5	А	
IGR	Reverse gate current	erse gate current -20		
IGF	Forward gate current	42	mA	
PT	Total power dissipation *1	42.8	W	
Tch	Channel temperature	175	deg.C	
Tstg	Storage temperature	-65 / +175	deg.C	



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ECTRICAL CHARACTERISTICS	(Ta=25 deg.C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Тур.	Max.	Unit
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	-	7.5	А
gm	Transconductance	VDS=3V, ID=2.2A	-	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V, ID=20mA	-	-	-4.5	V
P1dB	Output power at 1dB gain compression	1	38	39.5	-	dBm
GLP	Linear power gain	VDS=10V, ID(RF off)=2.4A, f=6.4~7.2GHz	7	9	-	dB
ID	Drain current		-	-	3	А
P.A.E.	Power added efficiency		-	28	-	%
IM3	3rd order IM distortion *1		-42	-45	-	dBc
Rth(ch-c)	Thermal resistance *2	Delta Vf method	-	-	3.5	deg.C/W
*1 · item -51	2 tone test Po=28dBm Single Carrier I	evel f-7.2GHz Delta f-10MHz				

1 : item -51, 2 tone test, Po=28dBm Single Carrier Level, f=7.2GHz, Delta t=10MHz

*2 : Channel to case



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